

Plastic-Encapsulate Transistors

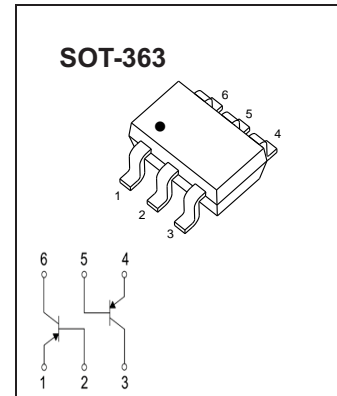
DUAL TRANSISTOR (PNP+PNP)

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: 5Ft

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)



Symbol	Parameter	Value	Units
V _{CB0}	Collector- Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-65	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS PNP 5401 (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-15	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-2mA	110		600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA			-0.1	V
		I _C =-100mA, I _B =-5mA *			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-0.5mA		0.7		V
Output Capacitance	C _{obo}	V _{CB} =-10V, f= 1MHz, I _E = 0			2.5	pF
Current Gain-Bandwidth Product	f _T	V _{CE} =-5V, I _C =-10mA, f= 100MHz	100			MHz

*pulse test: PW≤350μS, δ≤2%.

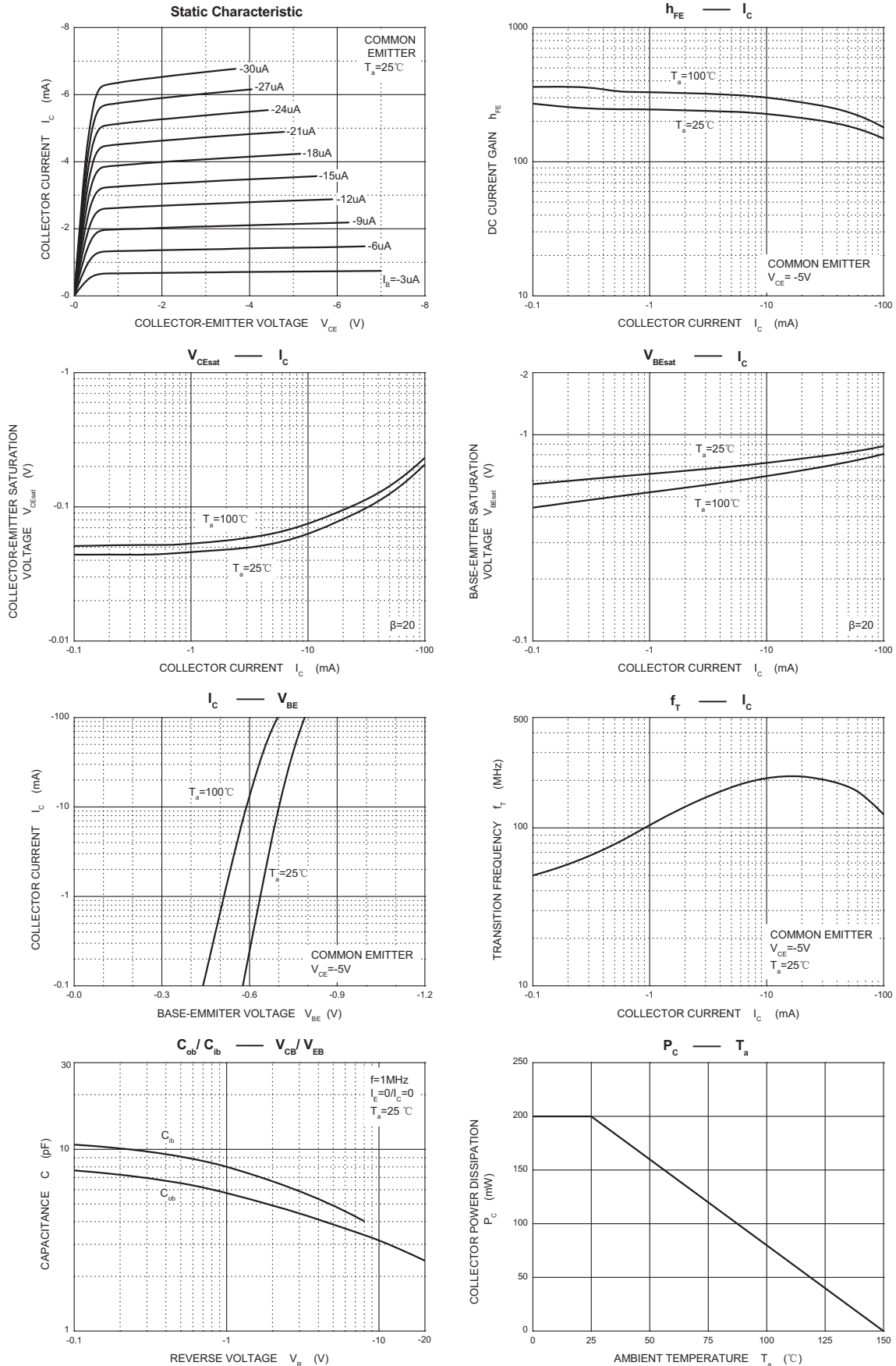


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SOT-363 BC856DW

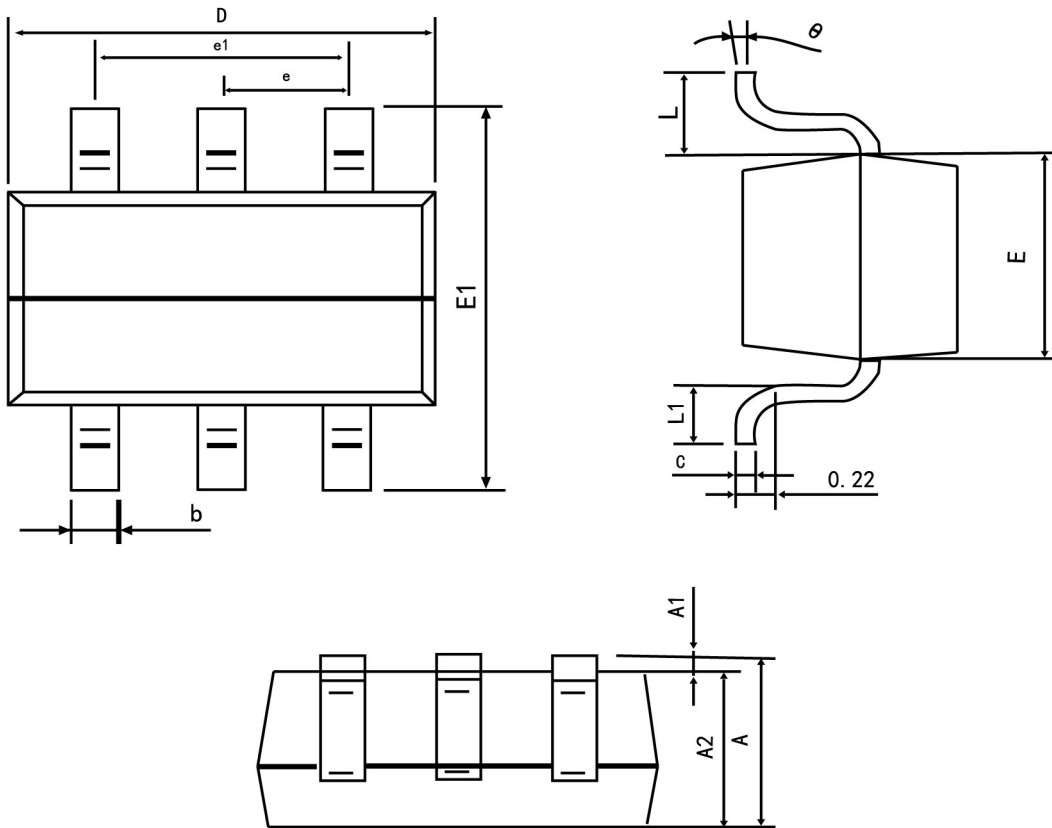


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SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°